

APS6401010001

940nm Multi Mode High Power VCSEL Array

II-VI's multimode high power VCSEL arrays are designed to meet stringent specifications for a broad range of optical 3D sensing applications. This product offers output powers of typically 3.5W with high efficiency and a rotation symmetrical beam profile. It is optimized for high volume consumer applications.

Features:

- Optical output power of 3.5W (QCW) at 940nm
- High efficiency and reliability
- Multi transverse mode emission
- Doughnut shaped, symmetrical farfield
- Non-hermetic operation
- Surface mountable

Applications:

- High volume time-of-flight (ToF) 3D sensing
- Illumination
- Industrial





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Electro-Optical Characteristics

All Electro-Optical parameters are specified at 25°C, pulsed (pulse length 2ms, 10% DC), unless otherwise noted.

Parameter	Symbol	0 1141	Ratings			11
		Conditions	Min	Тур	Max	Unit
Threshold Current	\mathbf{I}_{th}			1		А
Operating Current	I _{op}	P _{op} =4W		6	7.5	А
Power at 65°C	P _{op,65°C}	I=I _{op}		4		W
Operating Voltage	U _{op}	I=I _{op}		2	2.3	V
Differential Efficiency ¹	η_{diff}	I=I _{op}		0.95		W/A
Power Conversion Efficiency	PCE _{op}	I=I _{op}	30	38		%
Center Wavelength	λ_{center}	I=I _{op}	930	940	950	nm
Beam Divergence ²	θ _{FW1/e2}	I=I _{op}		24	28	0

¹ Defined as slope around operating current

Absolute Maximum Ratings

Parameter	Rating	Unit	Condition		
Continuous Operating Current	0.8	А	max 10 seconds		
Continuous Reverse Voltage	5	V	max 10 seconds		
PCB Solder or Reflow Temperature	260	°C	max 10 seconds		

Environmental Exposure Ratings

Parameter	Min	Тур	Max	Condition
Operating Environment				
Operating Temperature	0	65	°C	
Operating Humidity	0	80	%rH	non-condensing
Storage and Transport Environment				
Storage & Transport Temperature	-40	100	°C	
Storage & Transport Humidity	0	80	%rH	non-condensing

 $^{^{2}}$ FW1/e2 = full width 1/e2

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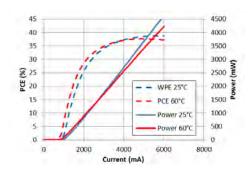
Packaging and Supply

- Sawn wafer on adhesive tape
- Wafer map files describing positions of good dice

Chip Dimensions

Parameter	Min	Тур	Max	Unit
Chip width		1334		μm
Chip length		1078		μm
Chip thickness	90	100	110	μm

Typical characteristics



1.E-04 9.E-05 8.E-05 7.E-05 8.E-05 9.E-05 9.

Figure 1: Power and PCE of VCSEL array measured on AIN surmount in pulsed mode at 10% Duty Cycle, 2ms pulse

Figure 2: Far Field emission profile at 4.5A, 2ms, 6% Duty Cycle

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RoHS Compliance





II-VI is fully committed to environment protection and sustainable development and has set in place a comprehensive program for removing polluting and hazardous substances from all of its products. The relevant evidence of RoHS compliance is held as part of our controlled documentation for each of our compliant products. RoHS compliance parts are available to order, please refer to the ordering information section for further details.

Ordering Information

Product Code Description

APS6401010001 940nm Multi Mode High Power VCSEL Array

Important Notice

Performance figures, data and any illustrative material provided in this data sheet are typical and must be specifically confirmed in writing by II-VI before they become applicable to any particular order or contract. In accordance with the II-VI policy of continuous improvement specifications may change without notice. Further details are available from any II-VI sales representative.

Safety Labels







